

Collector connected to case

**PNP** silicon annular transistors for high-frequency general-purpose amplifier applications.

## MAXIMUM RATINGS

Rating	Symbol	Types	Value	Unit
Base Voltage	v <sub>CB</sub>	2N869 2N995	25 20	Vdc
Collector-Emitter Voltage	V <sub>CEO</sub>	2N869 2N995	18 15	Vdc
Emitter-Base Voltage	VEB	2N869 2N995	5.0 4.0	Vdc
Total Device Dissipation at 25 <sup>o</sup> C Case Temperature at 100 <sup>o</sup> C Case Temperature Derate above 25 <sup>o</sup> C	PD	Both Types	1.2 0.68 6.86	Watts Watt mW/ <sup>0</sup> C
Total Device Dissipation at 25 <sup>0</sup> C Ambient Temperature Derate above 25 <sup>0</sup> C	P <sub>D</sub>	Both Types	0.36 2.06	Watt mW/ <sup>0</sup> C
Storage Temperature	T <sub>stg</sub>	Both Types	-65 to +200	°C
Junction Temperature	т <sub>Ј</sub>	Both Types	+200	°c

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
Collector-Base Breakdown Voltage $(I_C = 10 \ \mu \text{ Adc}, I_E = 0) \qquad 2N869$ 2N995	BV <sub>CBO</sub>	25 20			Vdc
Collector-Emitter Sustaining Voltage <sup>(1)</sup> (IC = 10 mAdc, I <sub>B</sub> = 0) 2N869 2N995	V <sub>CEO</sub> (sust)	18 15			Vdc
Emitter-Base Breakdown Voltage ( $I_E = 10 \mu Adc, I_C = 0$ ) 2N869 2N995	bv <sub>ebo</sub>	5.0 4.0			Vdc
$      Collector Cutoff Current \\ (V_{CB} = 15 Vdc, I_E = 0) 2N869 \\ 2N995 \\ (V_{CB} = 15 Vdc, I_E = 0, T_A = 150^{O}C) \  \  Both Types $	I <sub>CBO</sub>			010 005 25	μ Adc
$\begin{array}{llllllllllllllllllllllllllllllllllll$	I <sub>EBO</sub>			10	µ Adc
Collector Saturation Voltage $(I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc})$ 2N869 $(I_C = 20 \text{ mAdc}, I_B = 2.0 \text{ mAdc})$ 2N995	V <sub>CE</sub> (sat)		0. 17 	1.0 0.2	Vdc
Base Saturation Voltage ( $I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc}$ ) 2N869 ( $I_C = 20 \text{ mAdc}, I_B = 2.0 \text{ mAdc}$ ) 2N995	V <sub>BE</sub> (sat)		0. 78 	1.0 0.95	Vdc
	h <sub>FE</sub>	20 25 35 25		120  140 	
Open-Circuit Output Capacitance ( $V_{CB} = 10 V, I_E = 0$ ) 2N869 2N995	C <sub>ob</sub>		3.0 3.0	9 10	pF
Open-Circuit Input Capacitance ( $V_{BE} = 0.5 V, I_C = 0$ ) Both Types	C <sub>ib</sub>		7.0	11	pF
Small-Signal Forward-Current Transfer Ratio ( $I_C = 10 \text{ mA}, V_{CE} = 15 \text{ V}, f = 100 \text{ MHz}$ ) 2N869 ( $I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V}, f = 100 \text{ MHz}$ ) 2N995	h <sub>fe</sub>	1.0 1.0	3.0 3.0		

<sup>(1)</sup> Pulse Note: Pulse Width = 300  $\mu$  s, Duty Cycle = 1%